AMENDMENTS TO THE SPECIFICATION

Please amend the specification by replacing the paragraph that begins on specification page 2, line 21, and ends on specification page 3, line 9, with the following paragraph:

In order to solve this problem, it is known, as shown in FIG. 9 and FIG. 10, that on a glass substrate 2 in a sensor equivalent to the one described above, a short-circuit conductive pattern (equipotential wiring) 70 to electrically connect a fixed electrode 7 of the glass substrate 2 to a movable electrode of a silicon substrate 1 is formed in advance, and that when a high voltage is applied for anodic bonding, both electrodes are electrically connected via the equipotential wiring 70 ~~(refer e.g. to Japanese Laid-open Patent Publication Hei 10-090300)~~. This makes the fixed electrode equipotential to the silicon substrate in anodic bonding. Accordingly, discharge does not occur in anodic bonding, so that both electrodes are prevented from contacting and being fusion-bonded to each other, making it possible to obtain a high bonding strength as well. However, with the equipotential wiring being kept formed, desired sensor characteristics cannot be obtained.